

## Erratum

In the paper “Development of the magnetic tunnel junction MRAM at IBM: From first junctions to a 16-Mb MRAM demonstrator chip” by W. J. Gallagher and S. S. P. Parkin in the *IBM Journal of Research and Development*, Volume 50, No. 1, January 2006, the legend in Figure 1(d) should read  $T = 295$  K instead of 4.2 K. In the legend in Figure 5, the triangle and circle symbols were erroneously interchanged. The corrected figure appears below.

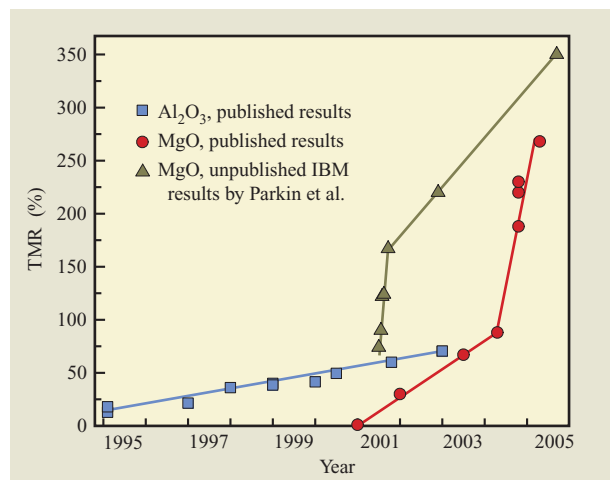


Figure 5

Maximum demonstrated TMR values over time for magnetic tunnel junctions with Al<sub>2</sub>O<sub>3</sub> and with MgO tunnel barriers.